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Zond LLC IPR2014-00861

GlobalFoundries U.S. Inc., GlobalFoundries Dresden Module One LLC & Co. I GlobalFoundries Dresden Module Two LLC & Co. KG, and The Gillette Comp

V.
Zond LLC

IPR2014-01088 and IPR2014-01089



# **Overview**

- Overview of the '652 Patent
- Grounds Instituted
- Overview of Prior Art
- Summary of Disputes with Respect to Independent Claims
- Summary of Disputes with Respect to Dependent Claims



## The '652 Patent

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(12) United States Patent

(10) Patent No.: US 6,806,652 B1 (45) Date of Patent: \*Oct. 19, 2004

(54) HIGH-DENSITY PLASMA SOURCE USING EXCITED ATOMS

(75) Inventor: Roman Chistyakov, Andover, MA
(US)

(73) Assignee: Zond, Inc., Mansfield, MA (US)

(\*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

This patent is subject to a terminal dis-claimer.

(22) Filed: May 12, 2003

#### Related U.S. Application Data

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(S2) U.S. Cl. J15/11.21; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24; 31/5/11.24;

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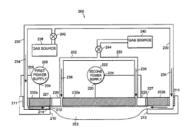
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#### ABSTRACT

35 Claims, 19 Drawing Sheets



TSMC-1101 TSMC v Zond, Inc.

(10) Patent No.: US 6,806, (45) Date of Patent: \*Oct.

HIGH-DENSITY PLASMA SOURG (54)**EXCITED ATOMS** 

IIS Patent 6 206 652 (Fx 1101



# **Independent Claims**

## Claim 1

# Claim 1 "Excited Atom Source"

- 1. A high-density plasma source comprising:
- a) a cathode assembly;
- b) an anode that is positioned adjacent to the cathode assembly;
- c) an excited atom source that generates an initial plasma and excited atoms from a volume of feed gas, the initial plasma and excited atoms being proximate to the cathode assembly; and
- d) a power supply that generates an electric field between the cathode assembly and the anode, the electric field super-ionizing the initial plasma so as to generate a high-density plasma.

'652 Patent, Claim 1 (Ex. 1101)



# **Independent Claims**

Claims 18 and 35

#### Claim 18

"Transporting the Initial Plasma and Excited Atoms"

- 18. A method of generating a high-density plasma, the method comprising:
  - a) generating an initial plasma and excited atoms from a volume of feed gas;
  - b) transporting the initial plasma and excited atoms proximate to a cathode assembly; and
  - c) super-ionizing the initial plasma proximate to the cathode assembly, thereby generating a high-density plasma.

Claim 35
"Transporting the Initial Place
Excited Atoms"

- 35. A high-density plasma source compris
- a) means for generating an initial plasm atoms from a volume of feed gas;
- b) means for transporting the initial plasm atoms proximate to a cathode assembly
- c) means for super-ionizing the initial plast to the cathode assembly, thereby gene density plasma.

'652 Patent, Claim 18 (Ex. 1101)

'652 Patent, C



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